Schottky Devices

HIGH POWER AND GENERAL PURPOSE SCHOTTKY DIODES

- Fast Switching
- Low Turn On Voltage
- Low Cost
- Tape and Reel Available

DESCRIPTION

This unique mesa construction (GC9700, GC9701, and GC9702) provides high breakdown voltage with true Schottky characteristics without resorting to the use of a diffused guard ring. The GC9703 and GC9704 are planar schottky devices. The standard devices are available in glass axial leaded packages as well as in chip form. Custom package styles are available on request.

APPLICATIONS

General high speed switching. High level mixers and detectors. Bridge quads for sampling circuits. Well suited for pulse shaping as well as limiting requirements.

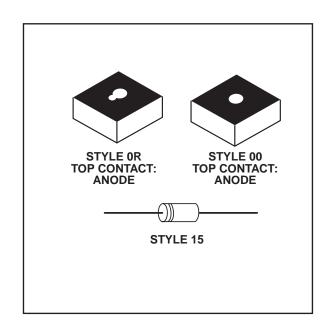


TABLE 1: ELECTRICAL CHARACTERISTICS AT TA=25°C

P/N	CASE STYLES	V _b min I _r =10 μA (V)	C _{t0} max f=1 MHz (pF)	V _f max I _f =1.0 mA (mV)	I _f min V _f =1.0 V (mA)	I _r max (nA)	@ V _r (V)	T _I max (psec)
GC9700	0R 15	70	2.1	430	15	200	50	100
GC9701	0R 00 15	30	1.5	430	50	100	5	100
GC9702	0R 00 15	20	1.5	430	35	300	15	100
GC9703	00 15	8	1.2	350	10*	100	1	100
GC9704	00 15	5	0.8	600	10	100	1	100

^{*} $|_f$ (min) for the GC9703 is measured at $V_f = 0.5$ V.

